ABSTRACT OF DISCLOSURE

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The present invention aims at maintaining a low dielectric constant in a case of forming an interlayer insulation film by baking SOGA When a plate-like material to be treated W, on the surface of which an applying film is formed, is entered into an apparatus, an elevator means 3 is lowered, so that the plate-like material to be treated W comes close to the cool plate 2, and further N2 gas is introduced into the apparatus FURNACE equal to 1% before the surface concentration in the atmosphere is reduced to less temperature of the plate-like material to be treated W rises to 200°C. Thereafter, while maintaining the oxygen concentration to be less than or equal to 1%, the elevator-means-3 is elevated, so that the plate-like material to be treated W comes-close to the hot plate 1, WORKPIECE and the surface of the plate-like material to be treated W is heated to be greater than or FINALLY After such a condition is continued for a predetermined period of time. YNALLY his instance, the oxygen concentration in the atmosphere the temperature is lowered. is maintained to be less than or equal to 1% until the surface temperature of the plate-like material to be treated W lowers to 200°C.

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